

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = 25^\circ C$
30V	12m $\Omega$ @ $V_{GS} = 10V$	10A
	16m $\Omega$ @ $V_{GS} = 4.5V$	8.5A

## Features and Benefits

- 0.6mm profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMN3016LDFDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and ideal for use in:

- Battery Management Applications
- Power Management Functions
- DC-DC Converters

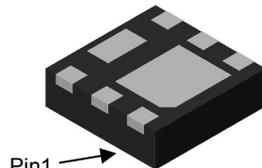
## Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.0065 grams (Approximate)

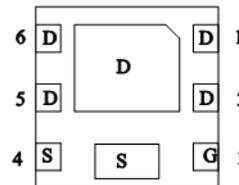
U-DFN2020-6 (Type F)



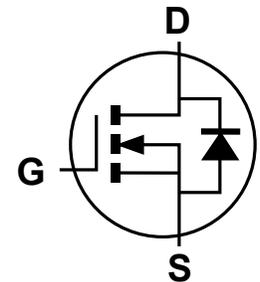
Top View



Bottom View



Pinout  
Bottom View



Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LDFDQ-7	U-DFN2020-6 (Type F)	3000/Tape & Reel
DMN3016LDFDQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

Site 1



NZ = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: 1 = 2021)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	I	J	K	L	M	N	O	P	R	S	T	U
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



NZ = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 1 = 2021)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026
Code	9	0	1	2	3	4	5	6
Week	1-26			27-52			53	
Code	A-Z			a-z			z	
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat	
Code	T	U	V	W	X	Y	Z	

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	10 8	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	12 9	A
Maximum Continuous Body Diode Forward Current (Note 5)			$I_S$	2.5	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	50	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			$I_{AR}$	22	A
Avalanche Energy (Note 7) $L = 0.1\text{mH}$			$E_{AR}$	24	mJ

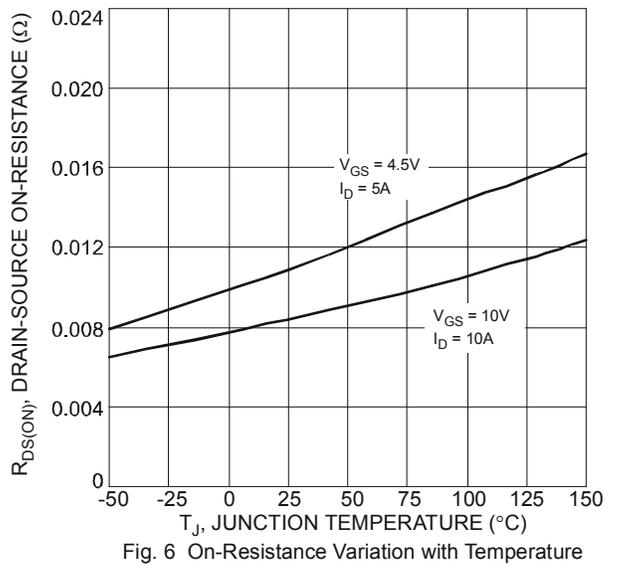
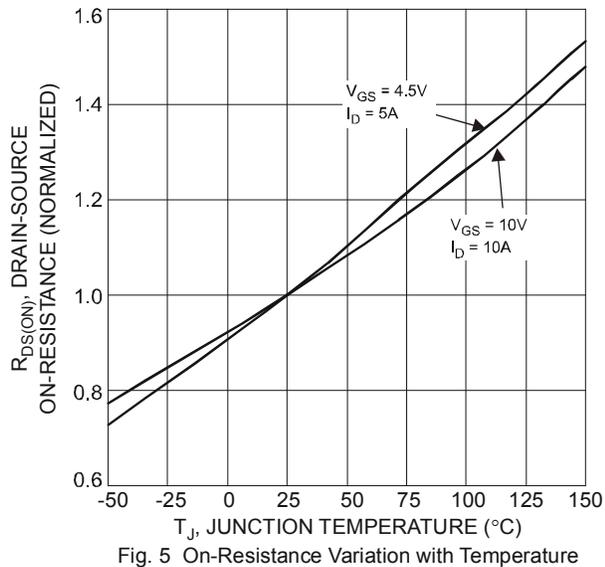
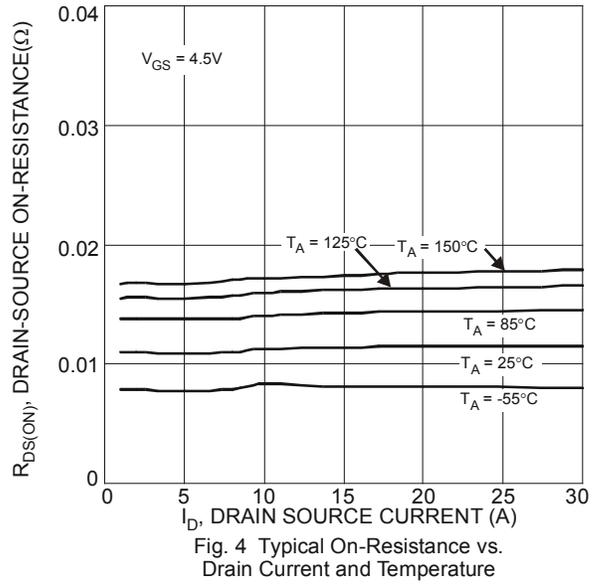
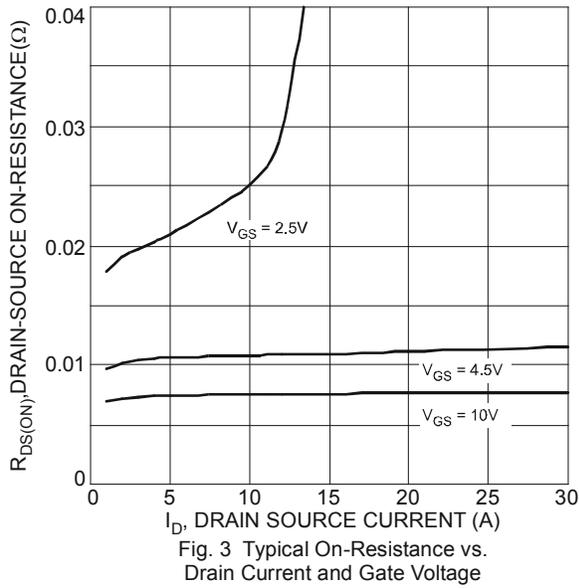
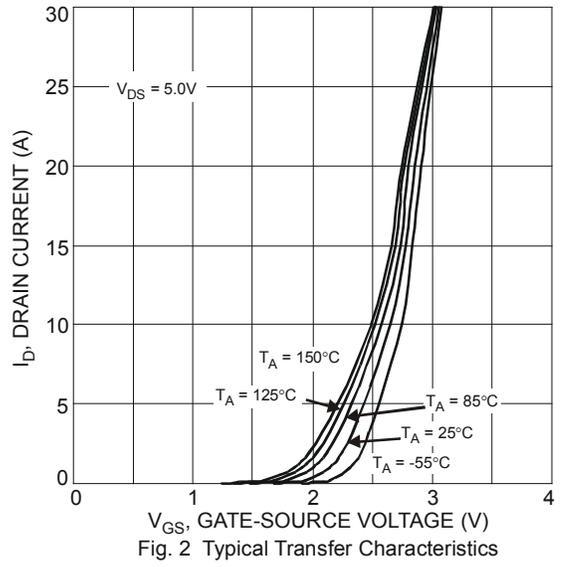
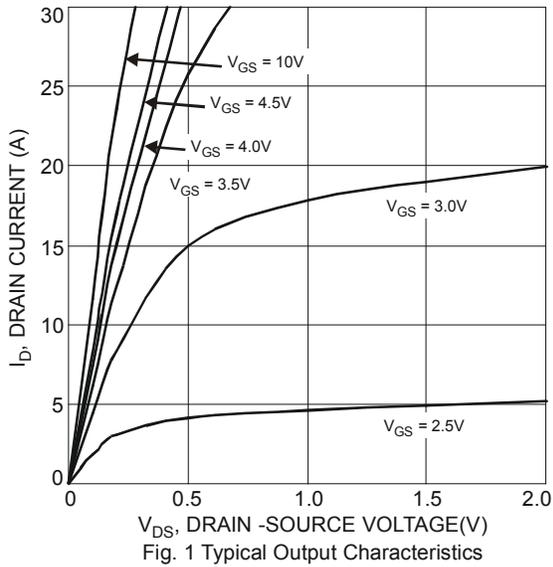
**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	$P_D$	0.73	W
	$T_A = +70^\circ\text{C}$		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	174	$^\circ\text{C/W}$
	$t < 10\text{s}$		121	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	$P_D$	2.02	W
	$T_A = +70^\circ\text{C}$		1.30	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	66	$^\circ\text{C/W}$
	$t < 10\text{s}$		42	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	11.6	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8	12	m $\Omega$	$V_{GS} = 10\text{V}, I_D = 11\text{A}$
		—	12	16		$V_{GS} = 4.5\text{V}, I_D = 9\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.70	1.0	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{ISS}$	—	1415	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	119	—		
Reverse Transfer Capacitance	$C_{RSS}$	—	82	—		
Gate Resistance	$R_g$	—	2.6	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	—	11.3	—	nC	$V_{DS} = 15\text{V}, I_D = 12\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_g$	—	25.1	—		
Gate-Source Charge	$Q_{GS}$	—	3.5	—		
Gate-Drain Charge	$Q_{GD}$	—	3.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.8	—	ns	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_L = 1.25\Omega, R_g = 3\Omega$
Turn-On Rise Time	$t_R$	—	16.5	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	26.1	—		
Turn-Off Fall Time	$t_F$	—	5.6	—		
Reverse Recovery Time	$t_{RR}$	—	12.3	—	ns	$I_F = 12\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{RR}$	—	10.4	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



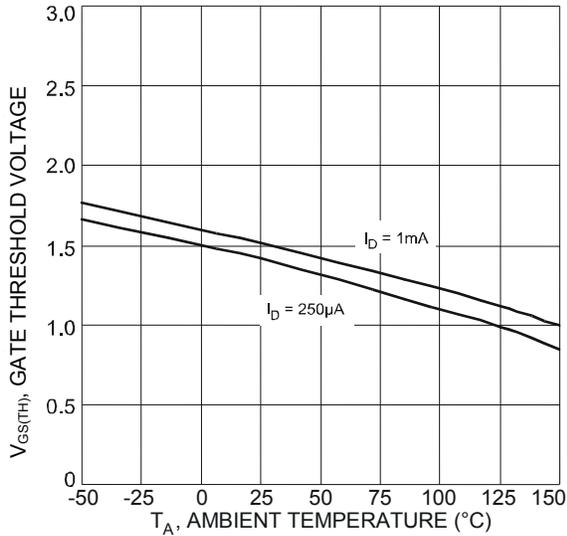


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

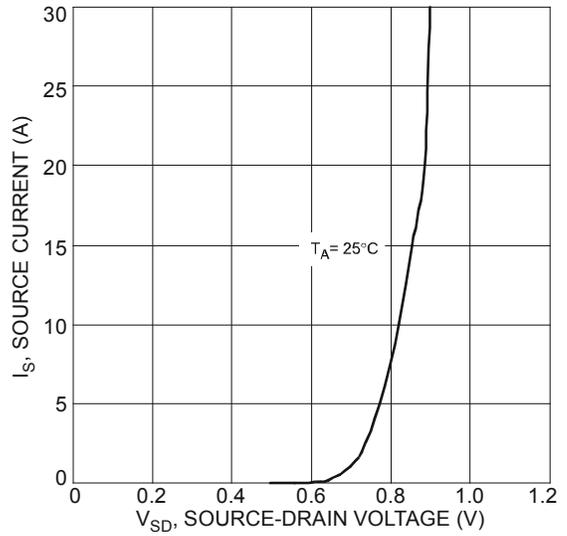


Fig. 8 Diode Forward Voltage vs. Current

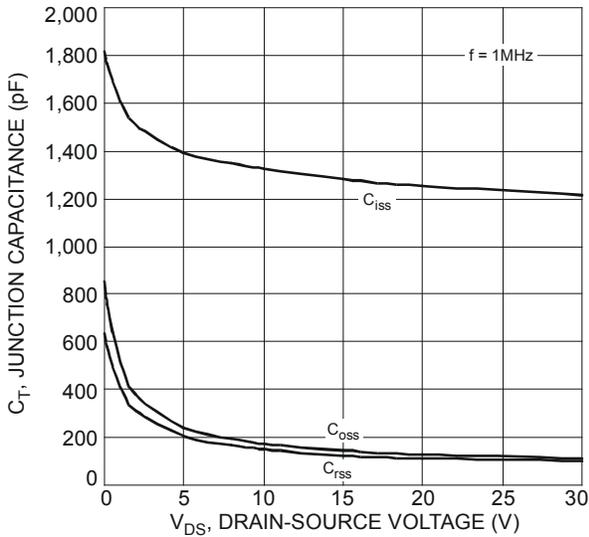


Fig. 9 Typical Junction Capacitance

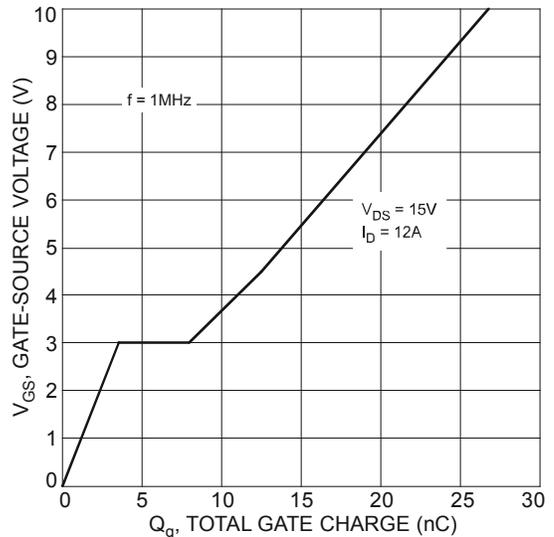


Fig. 10 Gate-Charge Characteristics

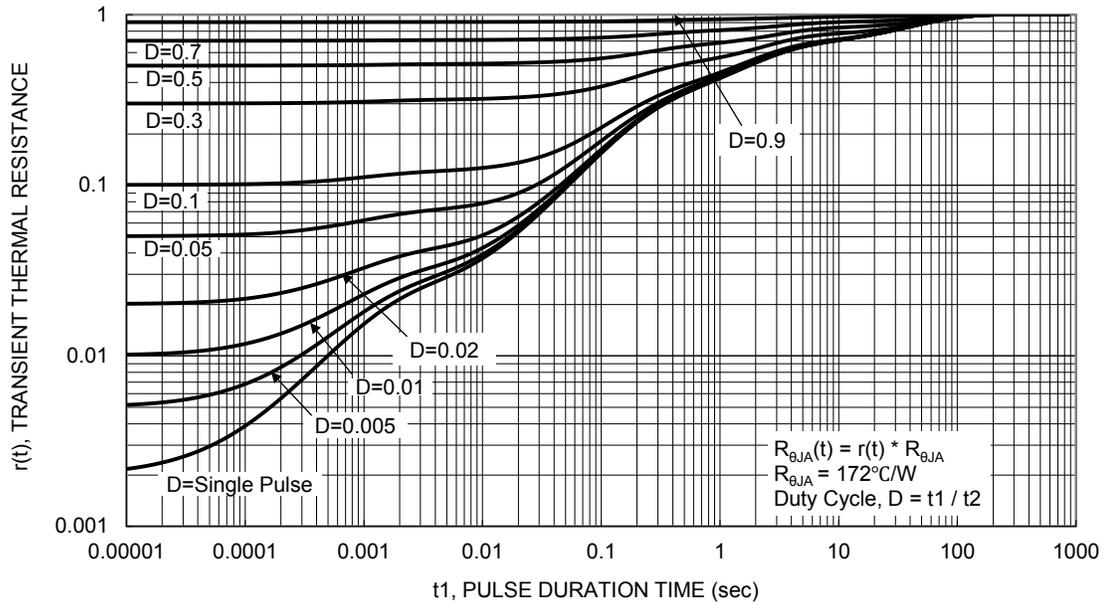
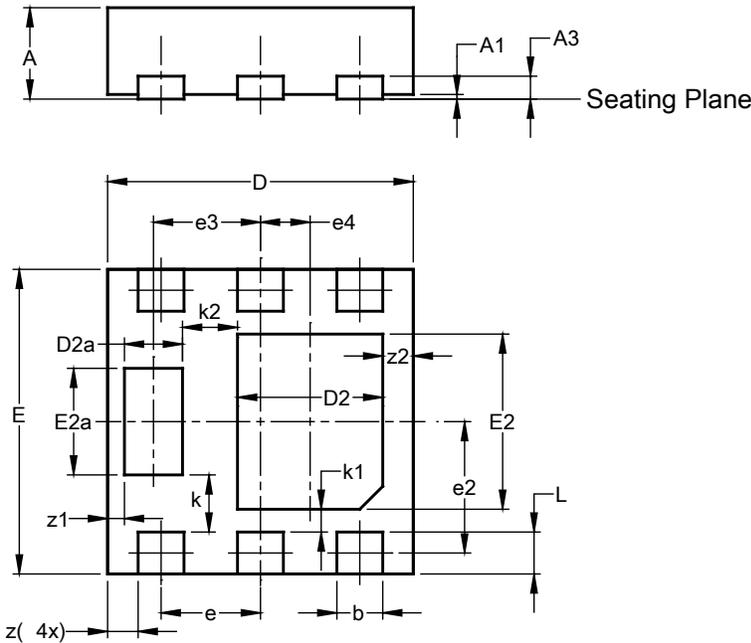


Figure 11. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**

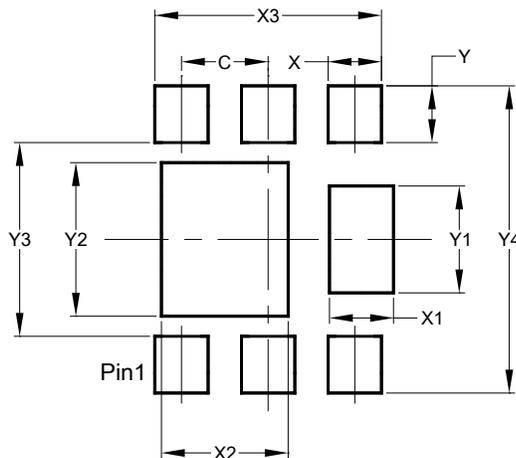


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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